

## Description:

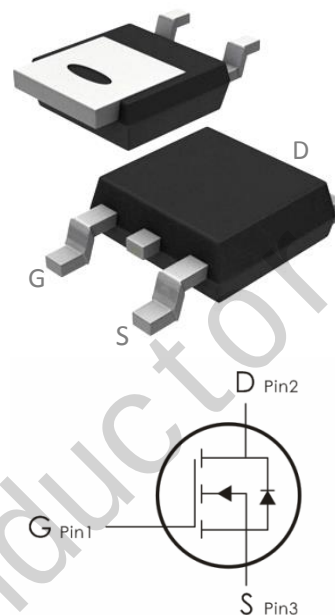
This N-Channel MOSFET uses advanced trench technology and

design to provide excellent  $R_{DS(on)}$  with low gate charge.

It can be used in a wide variety of applications.

## Features:

- 1)  $V_{DS}=60V, I_D=20A, R_{DS(on)} < 36m\Omega @ V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra  $R_{DS(on)}$ .
- 5) Excellent package for good heat dissipation.



## Absolute Maximum Ratings: ( $T_C=25^\circ C$ unless otherwise noted)

| Symbol         | Parameter                                        | Ratings     | Units      |
|----------------|--------------------------------------------------|-------------|------------|
| $V_{DS}$       | Drain-Source Voltage                             | 60          | V          |
| $V_{GS}$       | Gate-Source Voltage                              | $\pm 20$    | V          |
| $I_D$          | Continuous Drain Current- $T_C=25^\circ C$       | 20          | A          |
|                | Continuous Drain Current- $T_C=100^\circ C$      | 13          |            |
| $I_{DM}$       | Pulsed Drain Current <sup>note1</sup>            | 80          |            |
| $E_{AS}$       | Single Pulse Avalanche Energy <sup>note2</sup>   | 40          | mJ         |
| $P_D$          | Power Dissipation, $T_C=25^\circ C$              | 31          | W          |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range | -55 to +150 | $^\circ C$ |

## Thermal Characteristics:

| Symbol          | Parameter                            | Max | Units        |
|-----------------|--------------------------------------|-----|--------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 4   | $^\circ C/W$ |

Electrical Characteristics: ( $T_C=25^{\circ}\text{C}$  unless otherwise noted)

| Symbol                             | Parameter                                                | Conditions                                                                                 | Min | Typ  | Max   | Units |
|------------------------------------|----------------------------------------------------------|--------------------------------------------------------------------------------------------|-----|------|-------|-------|
| Off Characteristics                |                                                          |                                                                                            |     |      |       |       |
| BV <sub>DSS</sub>                  | Drain-Source Breakdown Voltage                           | V <sub>GS</sub> =0V, I <sub>D</sub> =250 μ A                                               | 60  | ---  | ---   | V     |
| I <sub>DSS</sub>                   | Zero Gate Voltage Drain Current                          | V <sub>GS</sub> =0V, V <sub>DS</sub> =60V                                                  | --- | ---  | 1     | μ A   |
| I <sub>GSS</sub>                   | Gate-Source Leakage Current                              | V <sub>GS</sub> =± 20V, V <sub>DS</sub> =0A                                                | --- | ---  | ± 100 | nA    |
| On Characteristics                 |                                                          |                                                                                            |     |      |       |       |
| V <sub>GS(th)</sub>                | GATE-Source Threshold Voltage                            | V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250 μ A                                 | 1   | 1.6  | 3     | V     |
| R <sub>DS(on)</sub>                | Drain-Source On Resistance <sup>note3</sup>              | V <sub>GS</sub> =10V, I <sub>D</sub> =10A                                                  | --- | 26   | 36    | m Ω   |
|                                    |                                                          | V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A                                                  | --- | 36   | 45    | m Ω   |
| Dynamic Characteristics            |                                                          |                                                                                            |     |      |       |       |
| C <sub>iss</sub>                   | Input Capacitance                                        | V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz                                          | --- | 1150 | ---   | pF    |
| C <sub>oss</sub>                   | Output Capacitance                                       |                                                                                            | --- | 55   | ---   |       |
| C <sub>rss</sub>                   | Reverse Transfer Capacitance                             |                                                                                            | --- | 45.3 | ---   |       |
| Switching Characteristics          |                                                          |                                                                                            |     |      |       |       |
| t <sub>d(on)</sub>                 | Turn-On Delay Time                                       | V <sub>DS</sub> =30V, I <sub>D</sub> =15A,<br>V <sub>GS</sub> =10V, R <sub>GEN</sub> =1.8Ω | --- | 7.6  | ---   | ns    |
| t <sub>r</sub>                     | Rise Time                                                |                                                                                            | --- | 20   | ---   | ns    |
| t <sub>d(off)</sub>                | Turn-Off Delay Time                                      |                                                                                            | --- | 15   | ---   | ns    |
| t <sub>f</sub>                     | Fall Time                                                |                                                                                            | --- | 24   | ---   | ns    |
| Q <sub>g</sub>                     | Total Gate Charge                                        | V <sub>GS</sub> =10V, V <sub>DS</sub> =30V,<br>I <sub>D</sub> =10A                         | --- | 20.3 | ---   | nC    |
| Q <sub>gs</sub>                    | Gate-Source Charge                                       |                                                                                            | --- | 3.7  | ---   | nC    |
| Q <sub>gd</sub>                    | Gate-Drain “Miller” Charge                               |                                                                                            | --- | 5.3  | ---   | nC    |
| Drain-Source Diode Characteristics |                                                          |                                                                                            |     |      |       |       |
| V <sub>SD</sub>                    | Source-Drain Diode Forward Voltage                       | V <sub>GS</sub> =0V, I <sub>S</sub> =20A                                                   | --- | ---  | 1.2   | V     |
| I <sub>S</sub>                     | Maximum Continuous Drain to Source Diode Forward Current |                                                                                            | --- | ---  | 20    | A     |
| I <sub>SM</sub>                    | Maximum Pulsed Drain to Source Diode Forward Current     |                                                                                            | --- | ---  | 80    | A     |

|            |                         |                                 |     |    |     |    |
|------------|-------------------------|---------------------------------|-----|----|-----|----|
| <b>trr</b> | Reverse Recovery Time   | $I_F = 10A, di/dt = 100A/\mu s$ | --- | 29 | --- | Ns |
| <b>qrr</b> | Reverse Recovery Charge |                                 | --- | 43 | --- | nc |

#### Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition :  $T_J = 25^\circ C, V_{DD} = 30V, V_G = 10V, L = 0.5mH, R_g = 25\Omega$
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 0.5\%$

#### Typical Characteristics: ( $T_C = 25^\circ C$ unless otherwise noted)

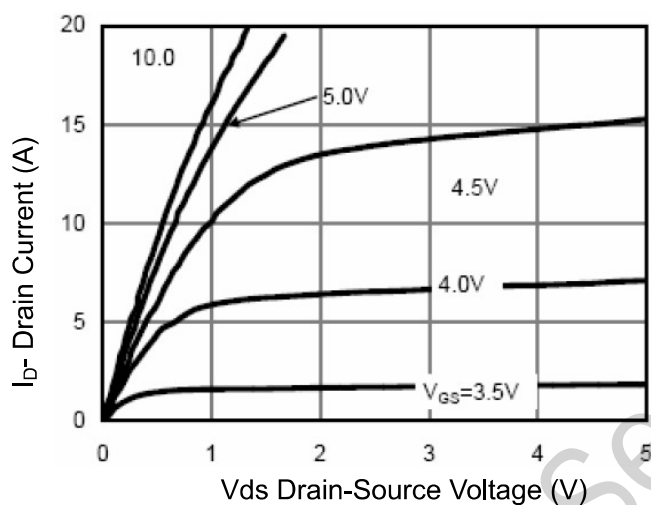


Figure 1 Output Characteristics

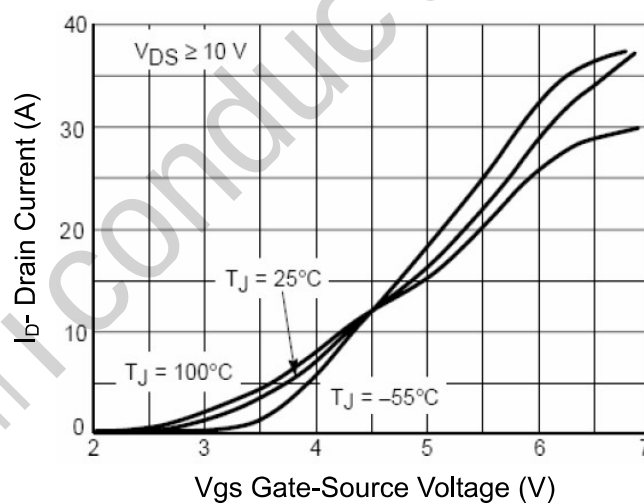


Figure 2 Transfer Characteristics

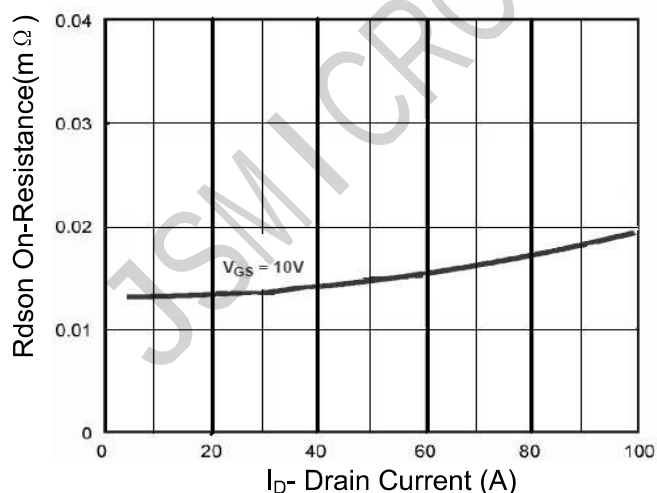


Figure 3 Rdson- Drain Current

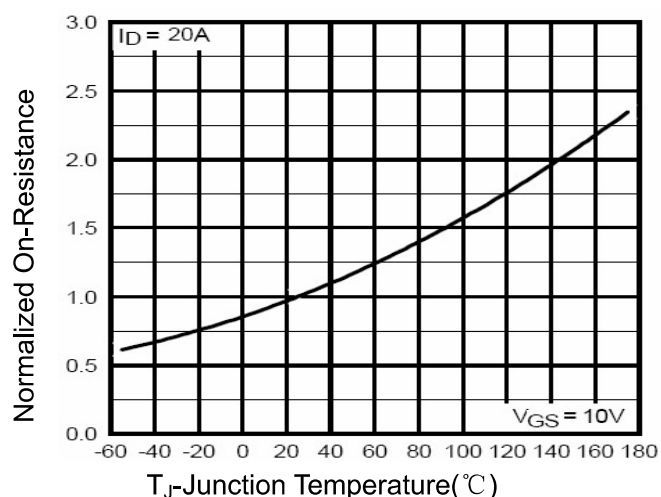


Figure 4 Rdson-Junction Temperature

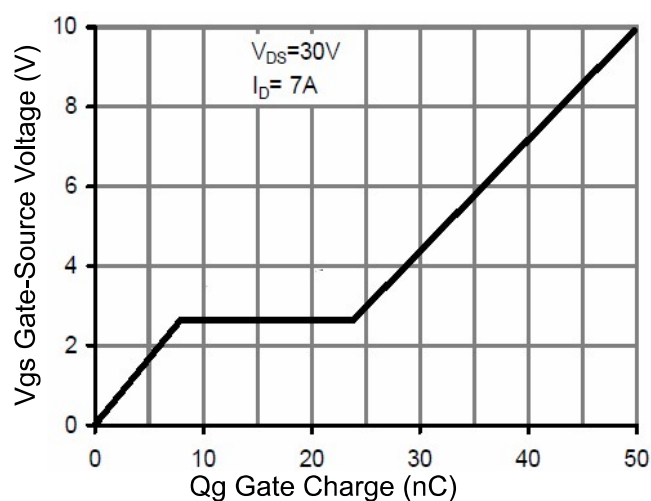


Figure 5 Gate Charge

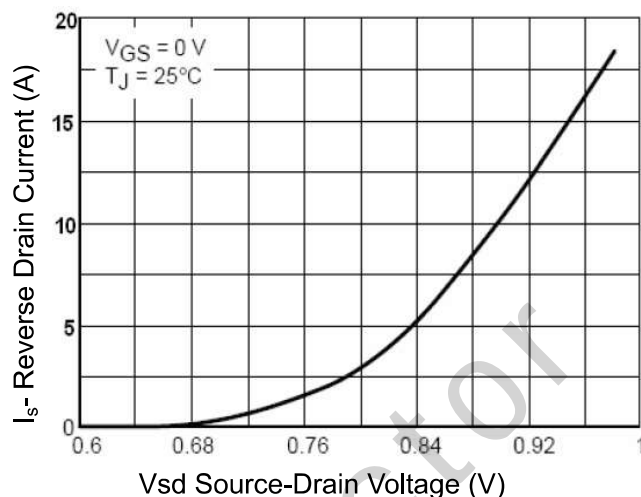


Figure 6 Source- Drain Diode Forward

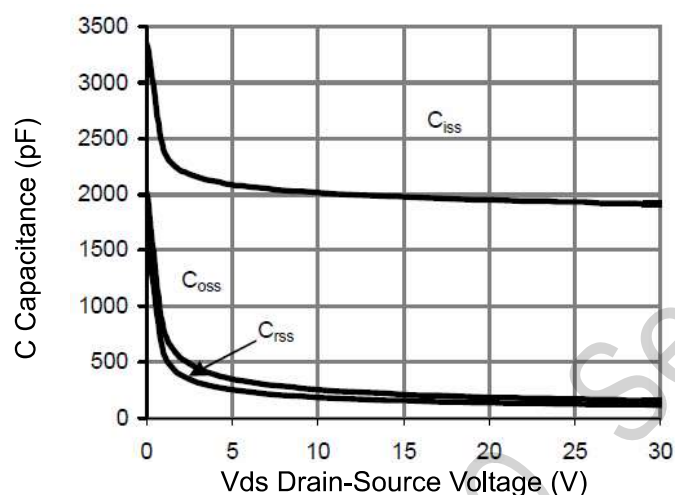


Figure 7 Capacitance vs Vds

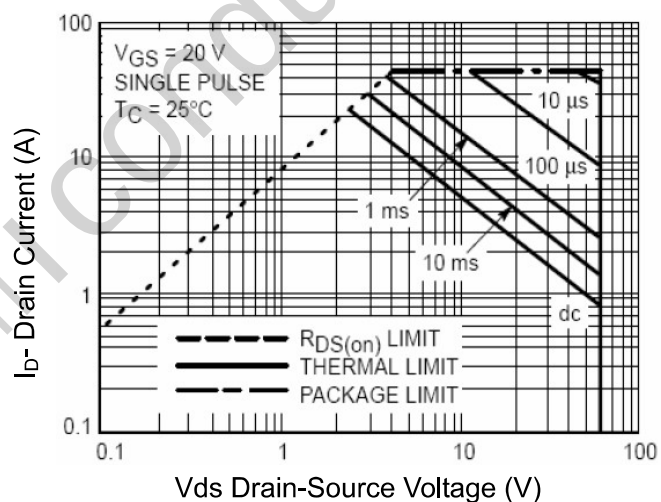


Figure 8 Safe Operation Area

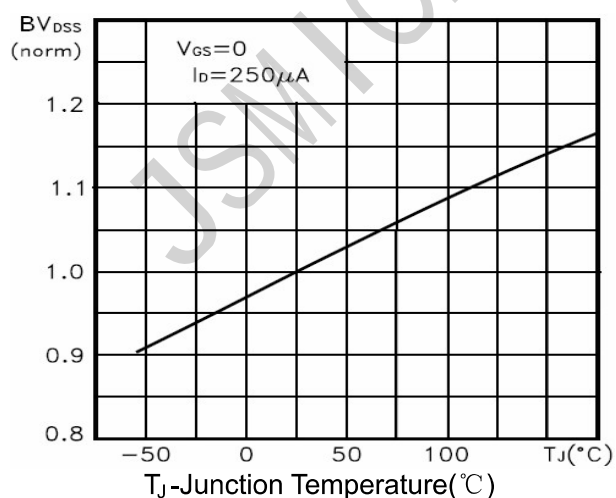


Figure 9 BV vs Junction Temperature

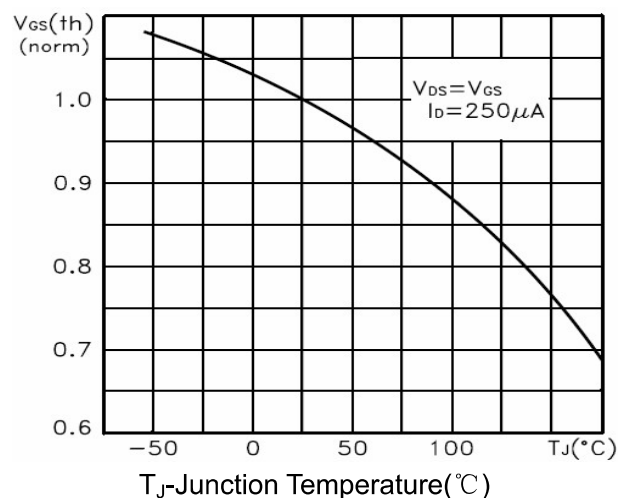
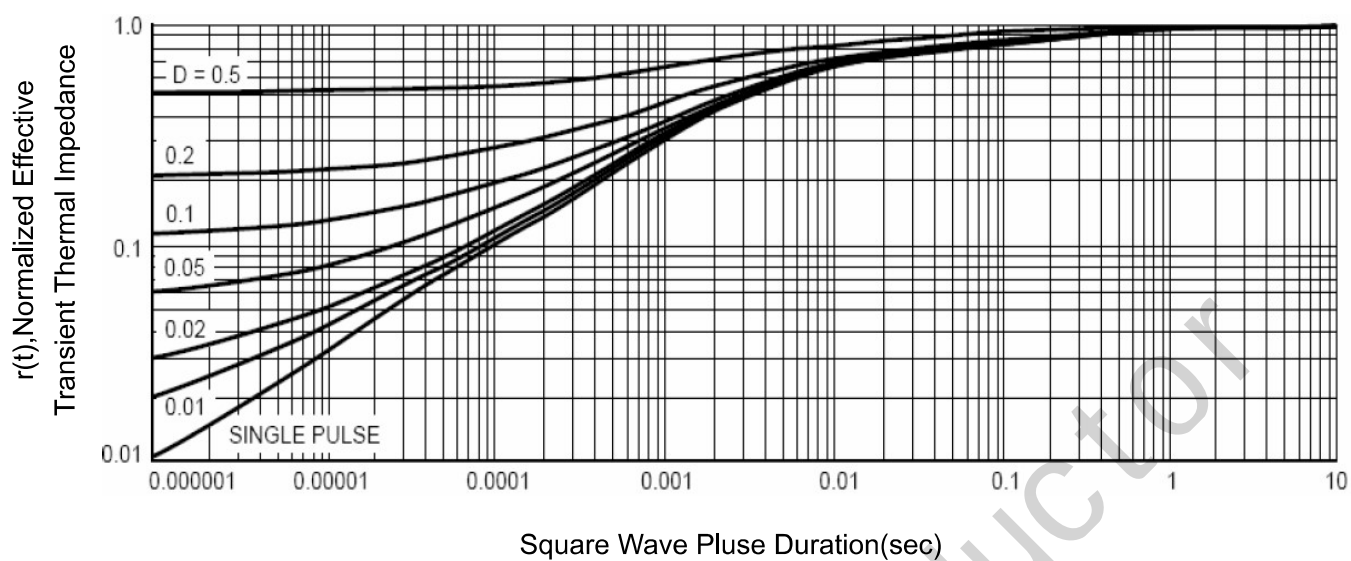


Figure 10  $V_{GS(th)}$  vs Junction Temperature



**Figure 11 Normalized Maximum Transient Thermal Impedance**

The technical drawing illustrates the geometry of a T0-252 component through four distinct views:

- Top View:** Shows a rectangular footprint with overall dimensions of 6.5 ±0.05 by 2.3 ±0.05. It features rounded corners with a radius of R 0.25~2X and chamfered edges at 7°~2X.
- Front View:** Displays the component's profile with a total height of 6.1 ±0.2. The base has a width of 5.4 ±0.2 and a central slot width of 3.9 ±0.2. A 20° chamfer is indicated on the left side.
- Side View:** Provides a cross-sectional view with a total length of 10.035 ±0.2. It shows internal features such as a 7° chamfer, a 0.508 wide slot, and various reference points (REF) for centering.
- Detail 'A':** A magnified view of the bottom corner, showing a 3°±3° angle and a 0.076 MAX ~6X feature.

Key dimensions and tolerances include: 6.5 ±0.05, 2.3 ±0.05, 6.1 ±0.2, 5.4 ±0.2, 3.9 ±0.2, 10.035 ±0.2, 0.508, 0.1, 1.01, 0.076 MAX ~6X, 0.8 ±0.1, 0.76~3X, 2.286, 5.06, 5.25, 0.1, 1.5, 25° REF, 3°±3°, and 7°.

单击下面可查看定价，库存，交付和生命周期等信息

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